

## Preliminary Amendment

### In the Specification

**[0024]** After forming the first conformal conductive layer, it is etched using a spacer etch which is selective to silicon nitride etch stop 80. A spacer etch which etches titanium nitride selective to silicon nitride to form titanium nitride spacers includes a plasma etch of nitrogen trifluoride ( $NF_3$ ) and chlorine ( $Cl_2$ ) for a duration of between about 5 seconds and about 20 seconds. This will clear the 50 Å - 100 Å layer of titanium nitride from the bottom of the opening in oxide layer 32 to result in the cross-sectional titanium nitride spacers 100 of FIG. 10. This etch may also remove a portion of the thickness from silicon nitride etch stop 80, but some will remain over pad 28. Additionally, a small percentage of the thickness of conductive layer 82 may be etched during this etch, but this will have no detrimental effect effect on processing or functionality of the device.